

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

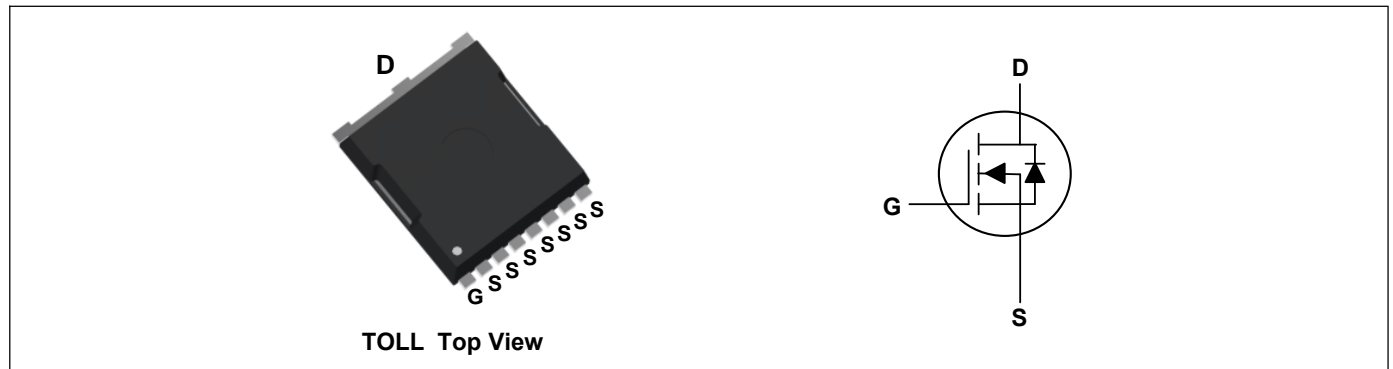
Product Summary



V_{DS}	120	V
I_D	225	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	3.5	m Ω

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application



Absolute Maximum Ratings($T_C=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_D@T_C=25^{\circ}C$	225	A
Continuous Drain Current ¹	$I_D@T_C=100^{\circ}C$	159	A
Pulsed Drain Current ²	I_{DM}	900	A
Single Pulse Avalanche Energy ³	E_{AS}	625	mJ
Total Power Dissipation ⁴	P_D	365	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	40	$^{\circ}C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	0.41	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	120	---	---	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	---	2.9	3.5	$m\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	---	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=120V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Gate Resistance	R_g	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.5	---	Ω
Total Gate Charge	Q_g	$V_{DS}=60V, V_{GS}=10V, I_D=20A$	---	145	---	nC
Gate-Source Charge	Q_{gs}		---	35	---	
Gate-Drain Charge	Q_{gd}		---	36	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DS}=60V, V_{GS}=10V, R_G=3\Omega, I_D=20A$	---	29	---	ns
Rise Time	T_r		---	50	---	
Turn-Off Delay Time	$T_{d(off)}$		---	88	---	
Fall Time	T_f		---	54	---	
Input Capacitance	C_{iss}	$V_{DS}=60V, V_{GS}=0V, f=1\text{MHz}$	---	8300	---	pF
Output Capacitance	C_{oss}		---	720	---	
Reverse Transfer Capacitance	C_{rss}		---	16	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage ²	V_{SD}	$V_{GS}=0V, I_S=20A, T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=55V, V_{GS}=10V, L=0.5\text{mH}$
- 4.The power dissipation is limited by 150°C junction temperature

Typical Characteristics

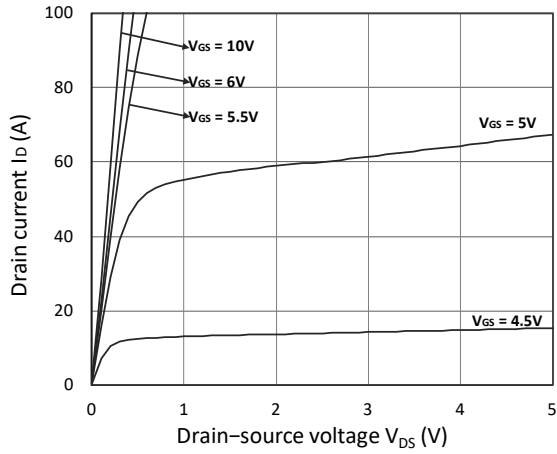


Figure 1. Output Characteristics

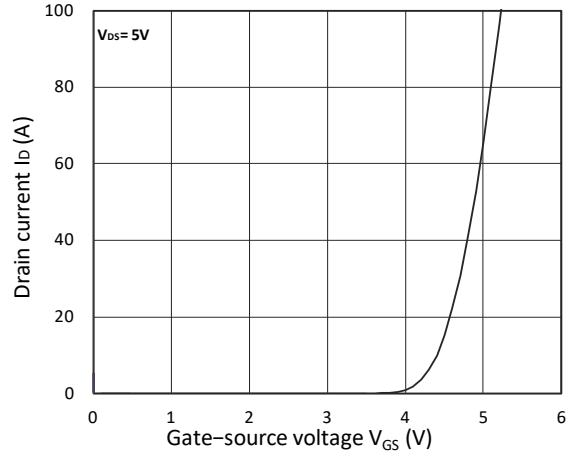


Figure 2. Transfer Characteristics

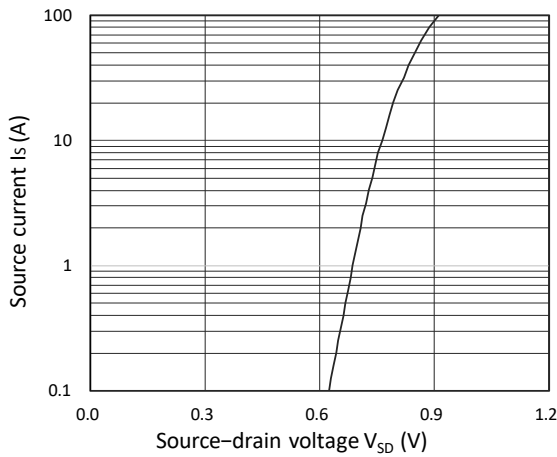


Figure 3. Forward Characteristics of Reverse

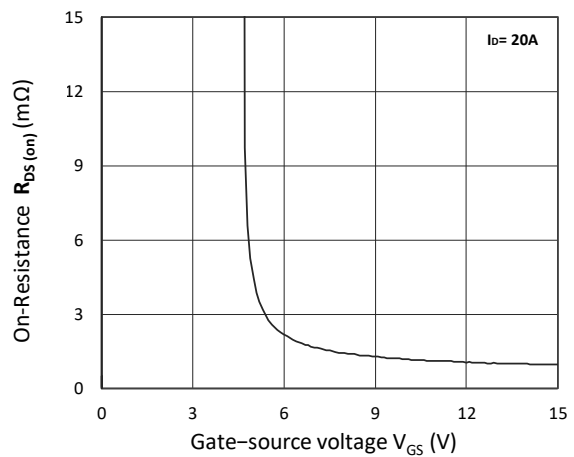


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

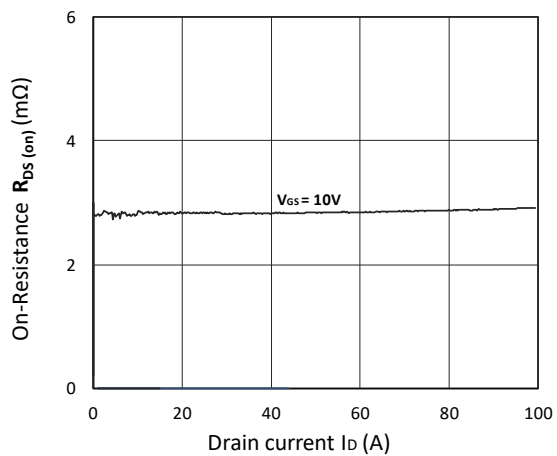


Figure 5. $R_{DS(ON)}$ vs. I_D

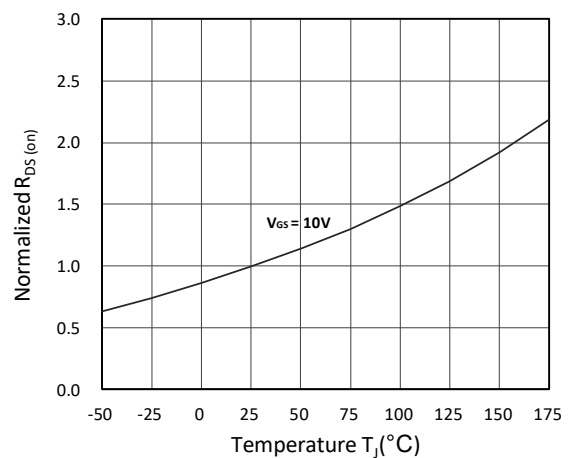


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

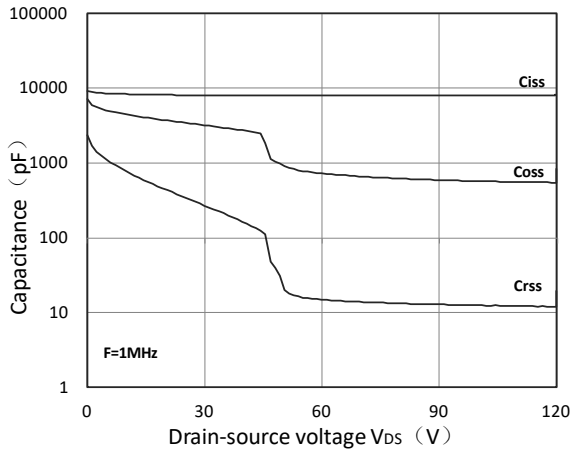


Figure 7. Capacitance Characteristics

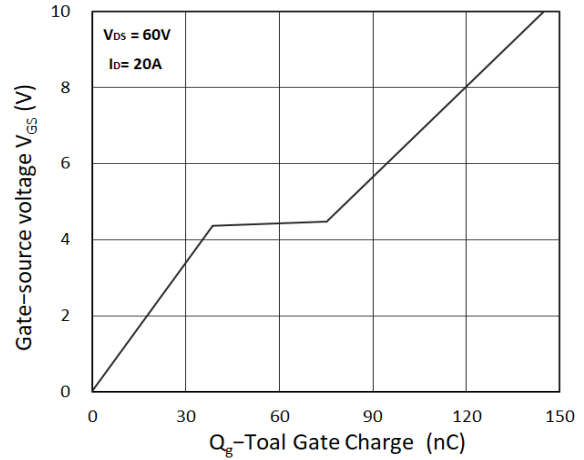


Figure 8. Gate Charge Characteristics

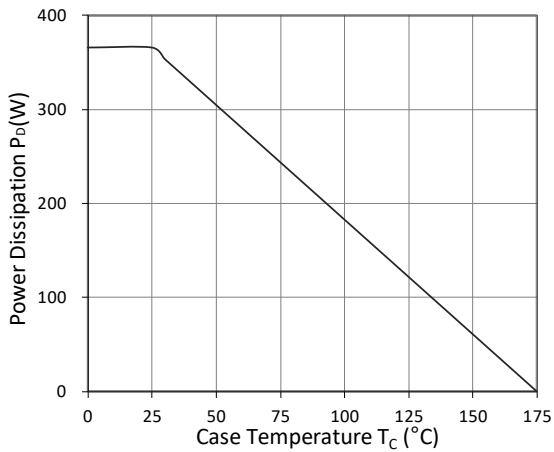


Figure 9. Power Dissipation

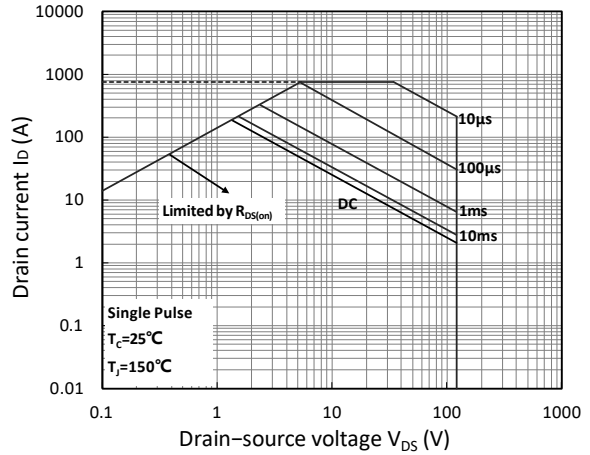


Figure 10. Safe Operating Area

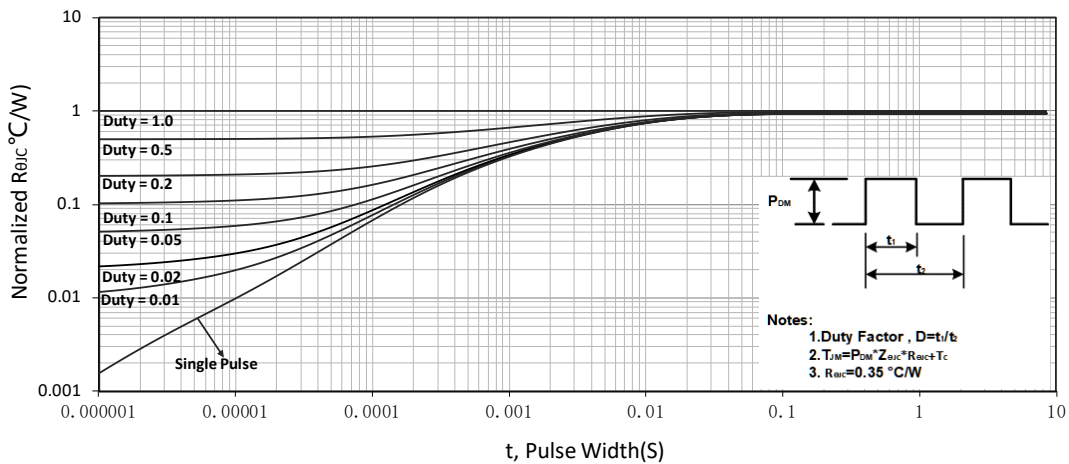
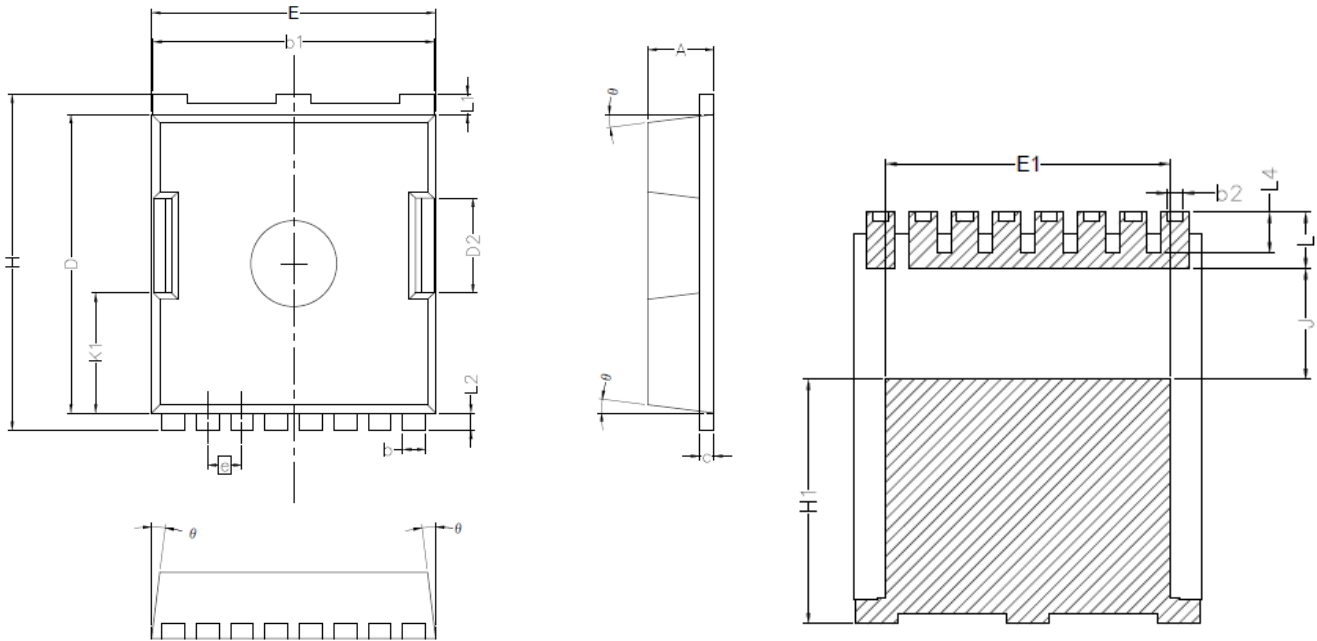


Figure 11. Normalized Maximum Transient Thermal Impedance

TOLL Package Outline Dimensions



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	2.20	2.40
b	0.90	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°

Printing Information

ATC =====Brand

XXXXXXX =====Material Code

XXYY =====XX Representative Year
 YY Representative Weeks